

SILICON BRIDGE RECTIFIERS

DB151--DB157

FEATURES

- Rating to 1000V PRVP
- Surge overload rating to 40 Amperes peak
- Glass passivated chip junctions
- Reliable low cost construction utilizing molded plastic technique results in inexpensive product
- Lead solderable per MIL-STD-202 method 208
- Lead: silver plated copper, solderde plated
- Plastic material has UL flammability classification94V-O



Maximum Ratings(@TA = 25°C unless otherwise specified)

Characteristic	Symbol	DB151	DB152	DB153	DB154	DB155	DB156	DB157	UNITS
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS Reverse Voltage	V_{RMS}	35	75	140	280	420	560	700	V
Maximum DC Blocking Voltage	V_{DC}	50	100	200	400	600	800	1000	V
Maximum average forward Output current @TA=25°C	$I_{F(AV)}$	1.5							A
Peak forward surge current 8.3ms single half-sine-wave superimposed on rated load	I_{FSM}	40							A

Thermal Characteristics

Characteristic	Symbol	DB151	DB152	DB153	DB154	DB155	DB156	DB157	UNITS
Operating junction temperature range	T_J	-55 -- +150							°C
Storage temperature range	T_{STG}	-55 -- +150							°C

Electrical Characteristics (@TA = 25°C unless otherwise specified)

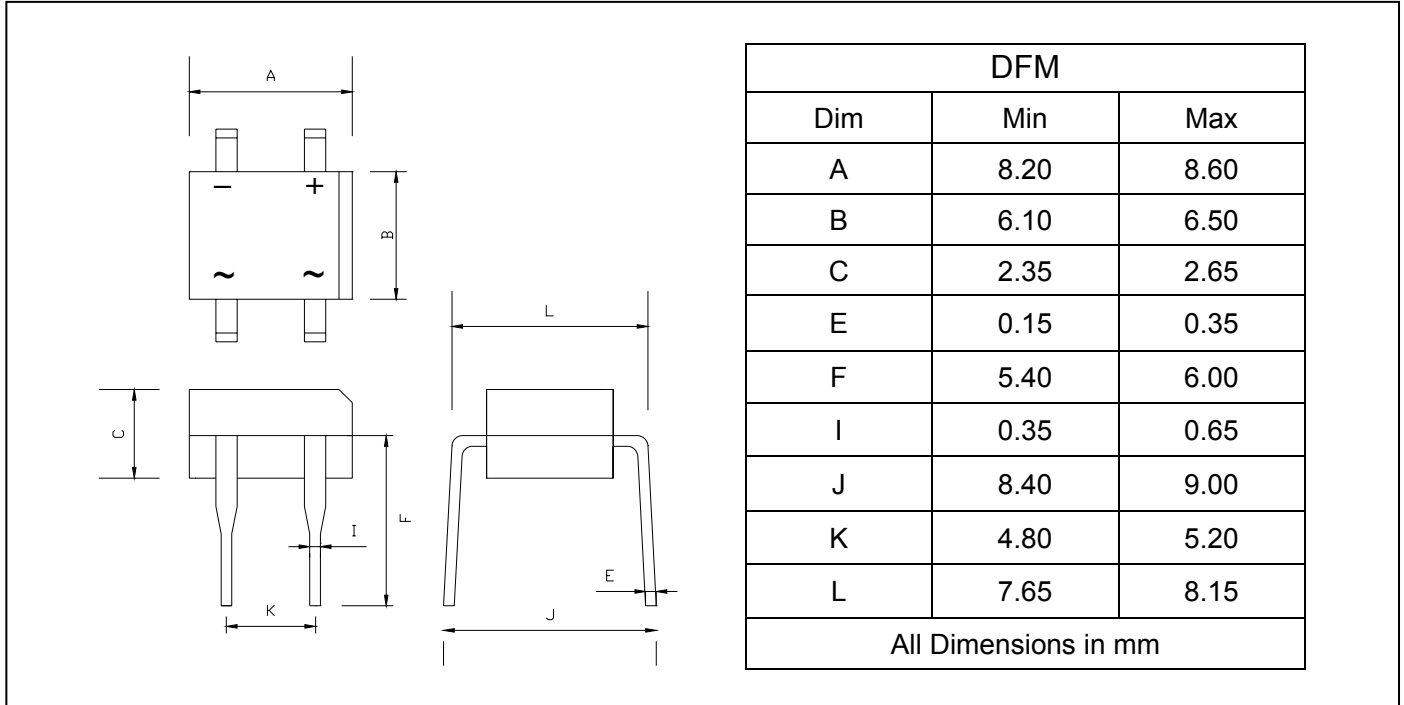
Characteristic	Symbol	DB151	DB152	DB153	DB154	DB155	DB156	DB157	UNITS
Maximum instantaneous forward voltage at 1.5A	V_F	1.1							V
Maximum reverse current @TA=25°C at rated DC blocking voltage @TA=100°C	I_R	5.0 0.5							μA mA



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PACKAGE OUTLINE DIMENSIONS



PACKAGE INFORMATION

Device	Package	Shipping
DB151--DB157	DFM	50unit/pipe



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FIG.1 -- PEAK FORWARD SURGE CURRENT

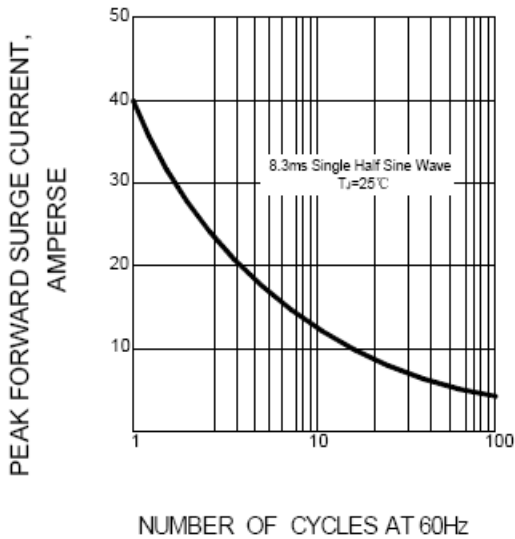


FIG.2 -- FORWARD DERATING CURVE

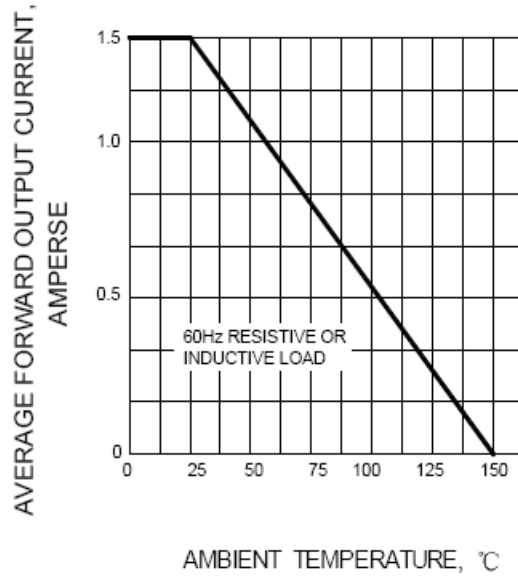


FIG.3 -- TYPICAL FORWARD CHARACTERISTIC

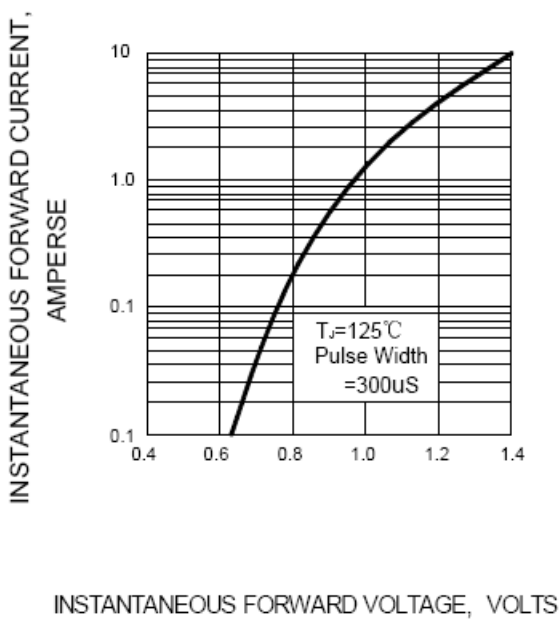


FIG.4 -- TYPICAL REVERSE CHARACTERISTIC

